

N-Channel Logic Level Enhancement Mode Power MOSFET

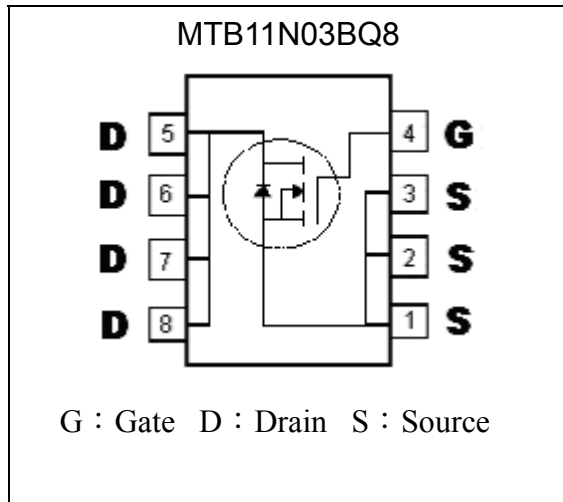
MTB11N03BQ8

BV_{DSS}	30V
$I_D@V_{GS}=10V, T_A=25^{\circ}C$	12A
$R_{DS(on)}(typ)@V_{GS}=10V, I_D=12A$	8.8mΩ
$R_{DS(on)}(typ)@V_{GS}=4.5V, I_D=12A$	12.8mΩ

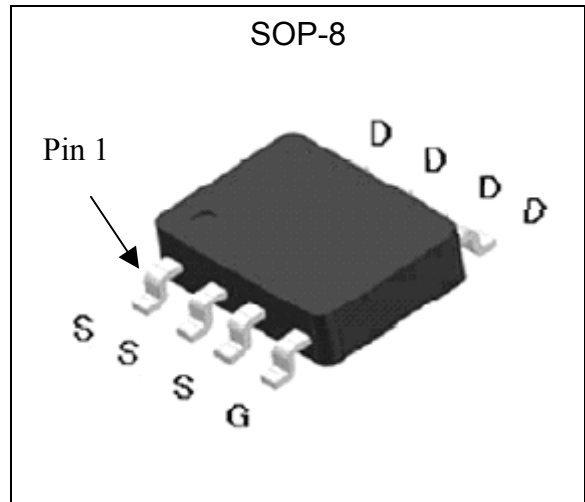
Features

- Single Drive Requirement
- Low On-resistance
- Fast Switching Characteristic
- Repetitive Avalanche Rated
- Pb-free and Halogen-free package

Symbol

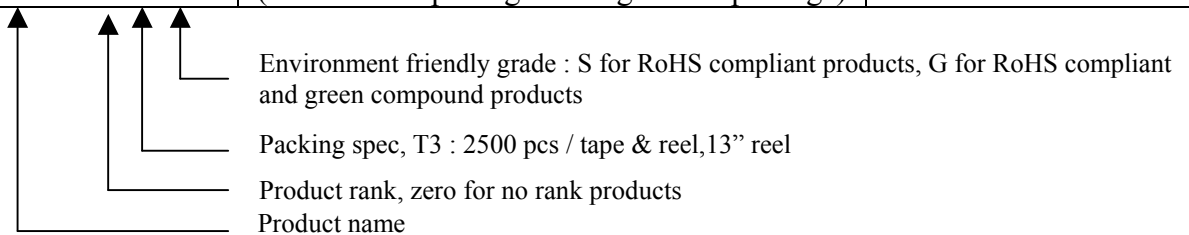


Outline



Ordering Information

Device	Package	Shipping
MTB11N03BQ8-0-T3-G	SOP-8 (Pb-free lead plating & halogen-free package)	2500 pcs / Tape & Reel





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	10s	Steady State	Unit
Drain-Source Voltage	V _{DS}	30		V
Gate-Source Voltage	V _{GS}	±25		
Continuous Drain Current @ TA=25°C, VGS=10V*3	I _D	12	8.3	A
Continuous Drain Current @ TA=70°C, VGS=10V*3		7.6	6.6	
Pulsed Drain Current	I _{DM}	48 *1		
Avalanche Current	I _{AS}	12		
Avalanche Energy @ L=1mH, I _D =12A, R _G =25Ω	E _{AS}	72		mJ
Repetitive Avalanche Energy @ L=0.05mH	E _{AR}	5 *2		
Total Power Dissipation *3	P _D	TA=25°C	1.4	W
		TA=70°C	0.9	
Operating Junction and Storage Temperature Range	T _j , T _{stg}	-55~+150		°C

Thermal Data

Parameter	Symbol	Typical	Maximum	Unit	
Thermal Resistance, Junction-to-ambient *3	R _{θJA}	t≤10s	35	40	°C/W
		Steady State	70	85	
Thermal Resistance, Junction-to case	R _{θJC}	16	25		

- Note : 1. Pulse width limited by maximum junction temperature.
 2. Duty cycle≤1%.
 3. Surface mounted on 1 in² copper pad of FR-4 board; 125°C/W when mounted on minimum copper pad.

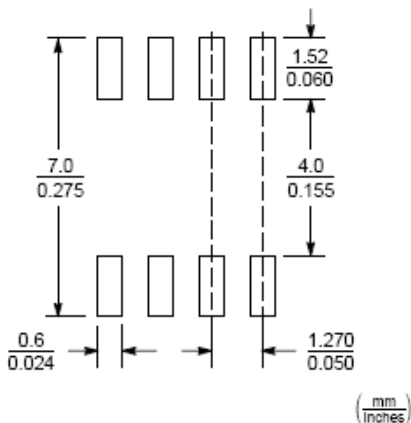
Characteristics (Tc=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	30	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	1.0	-	2.5		V _{DS} = V _{GS} , I _D =250μA
G _{FS} *1	-	19	-	S	V _{DS} =5V, I _D =11A
I _{GSS}	-	-	±100	nA	V _{GS} =±25V
I _{DSS}	-	-	1	μA	V _{DS} =30V, V _{GS} =0V
	-	-	5		V _{DS} =24V, V _{GS} =0V, T _j =55°C
R _{DS(ON)} *1	-	8.8	12	mΩ	V _{GS} =10V, I _D =12A
	-	12.8	17	mΩ	V _{GS} =4.5V, I _D =12A
Dynamic					
C _{iss}	-	751	-	pF	V _{GS} =0V, V _{DS} =10V, f=1MHz
C _{oss}	-	199	-		
C _{rss}	-	106	-		

Characteristics (Tc=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Qg (VGS=10V) *1, 2	-	15.9	-	nC	VDS=24V, VGS=10V, ID=11A
Qg (VGS=5V) *1, 2	-	9.6	-		
Qgs *1, 2	-	2.7	-		
Qgd *1, 2	-	4.7	-		
td(ON) *1, 2	-	9	-	ns	VDS=15V, ID=5.5A, VGS=10V, RGS=4.7Ω
tr *1, 2	-	17.4	-		
td(OFF) *1, 2	-	32.4	-		
tf *1, 2	-	10	-		
Rg	-	1.8	-	Ω	f=1MHz
Source-Drain Diode					
IS *1	-	-	12	A	
ISM *3	-	-	48		
VSD *1	-	0.84	1.3	V	IS=12A, VGS=0V
trr	-	10.3	-	ns	IF=11A, dIF/dt=100A/μs
Qrr	-	4.2	-	nC	

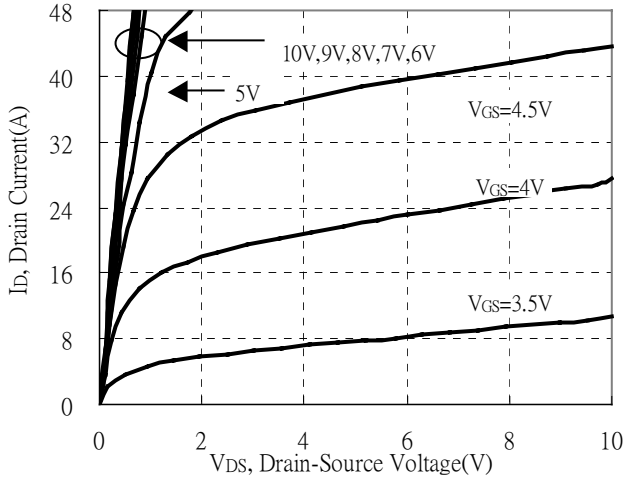
Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
 *2.Independent of operating temperature
 *3.Pulse width limited by maximum junction temperature.

Recommended Soldering Footprint


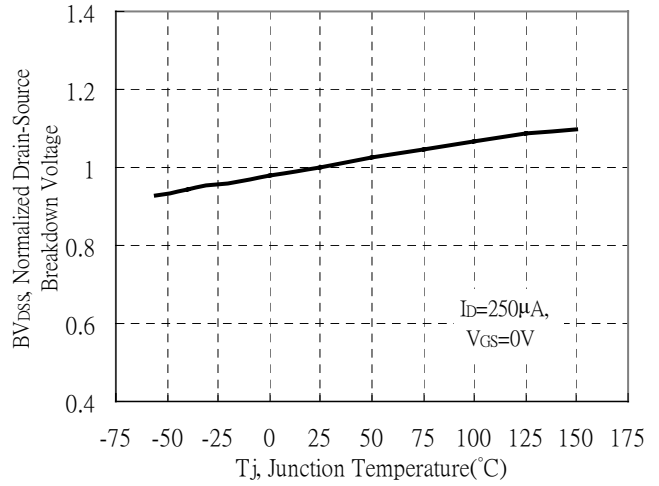


Typical Characteristics

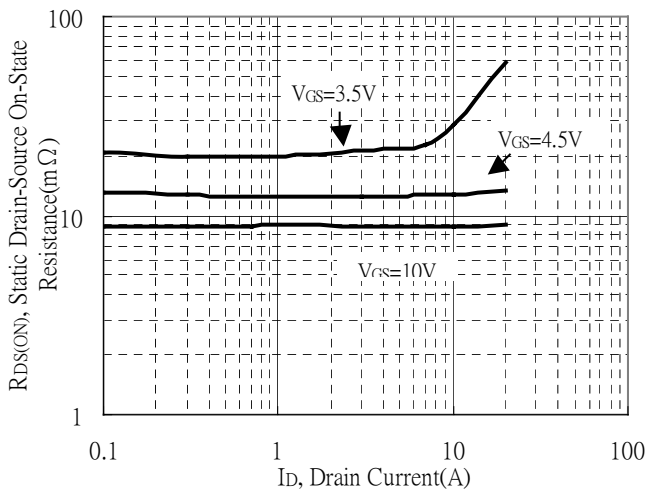
Typical Output Characteristics



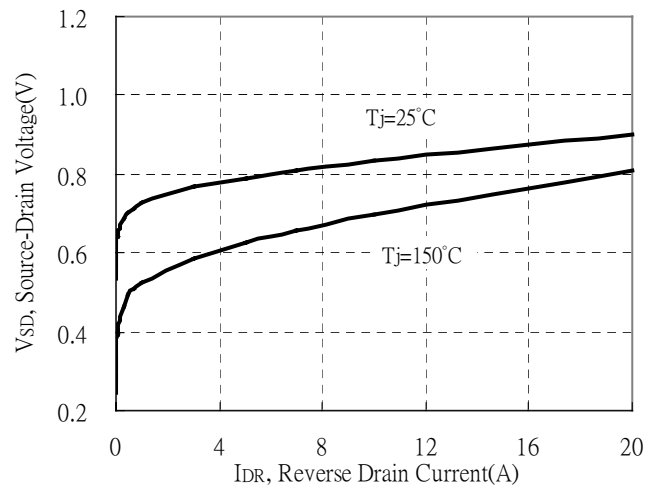
Brekdown Voltage vs Ambient Temperature



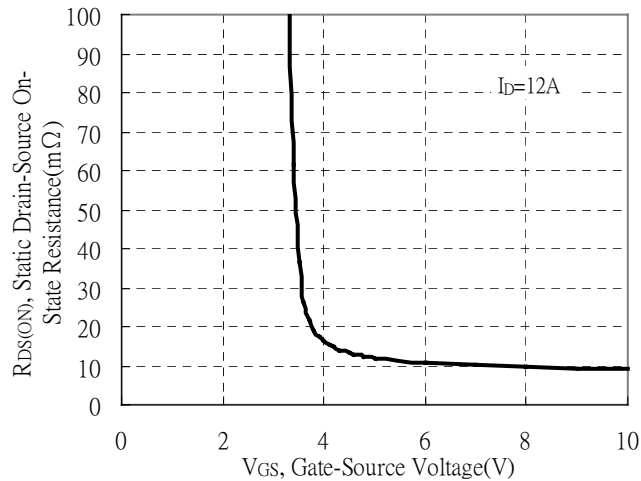
Static Drain-Source On-State resistance vs Drain Current



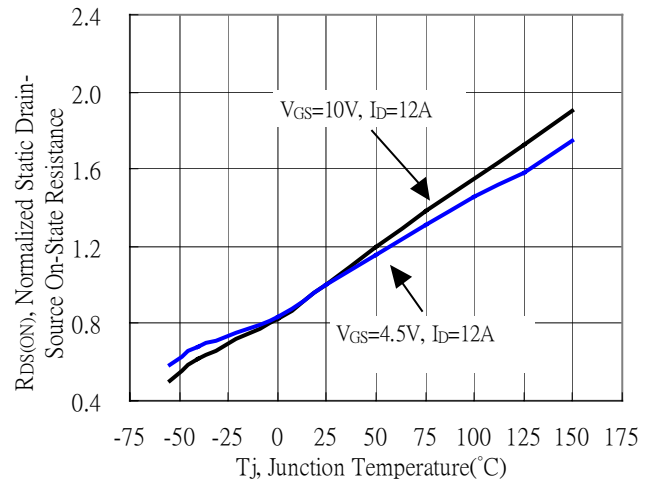
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

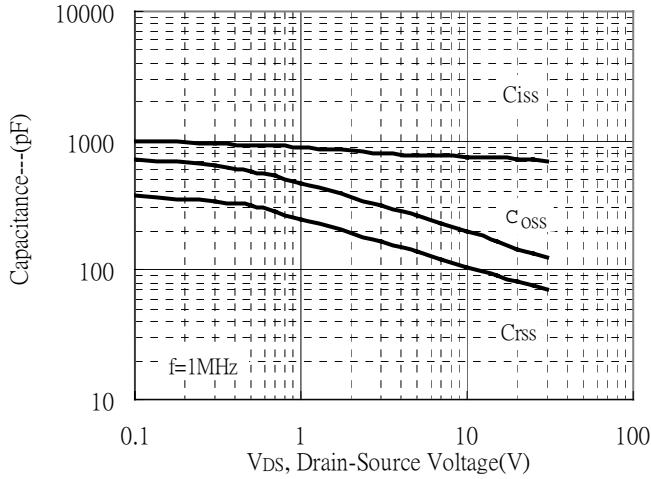


Drain-Source On-State Resistance vs Junction Temperature

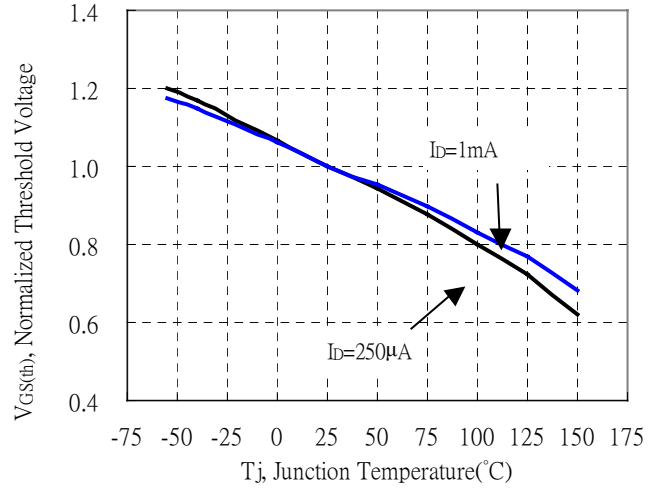


Typical Characteristics(Cont.)

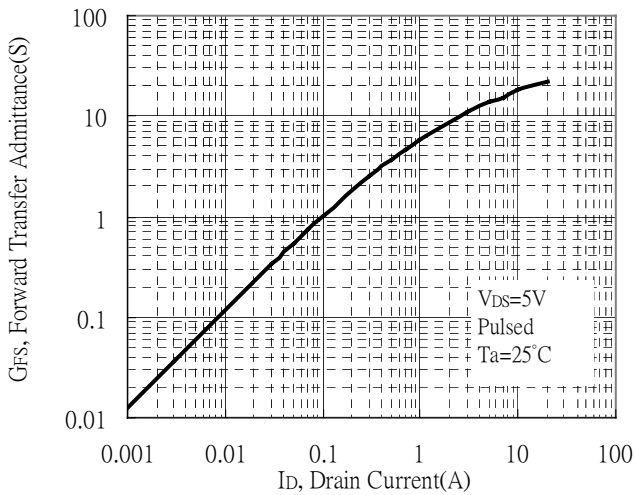
Capacitance vs Drain-to-Source Voltage



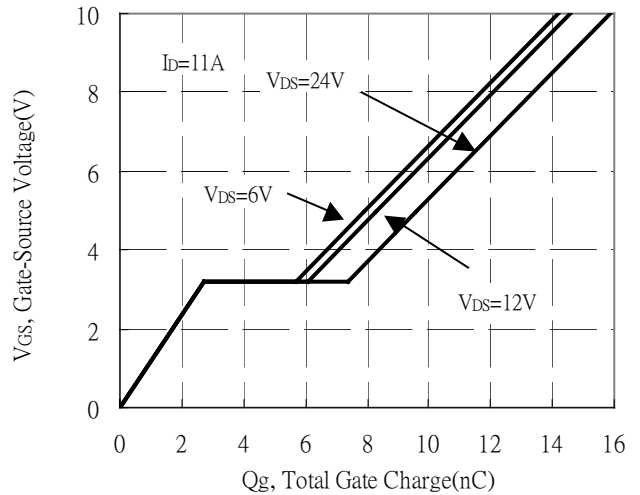
Threshold Voltage vs Junction Temperature



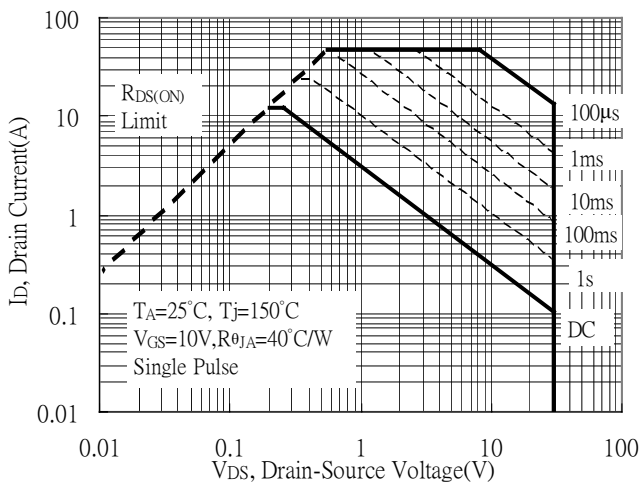
Forward Transfer Admittance vs Drain Current



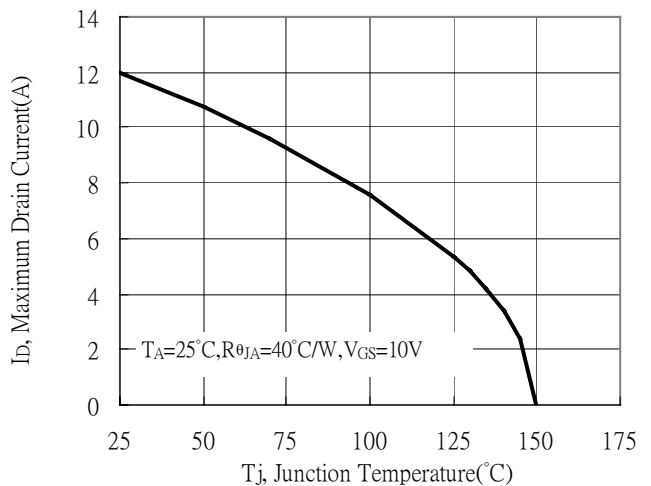
Gate Charge Characteristics



Maximum Safe Operating Area



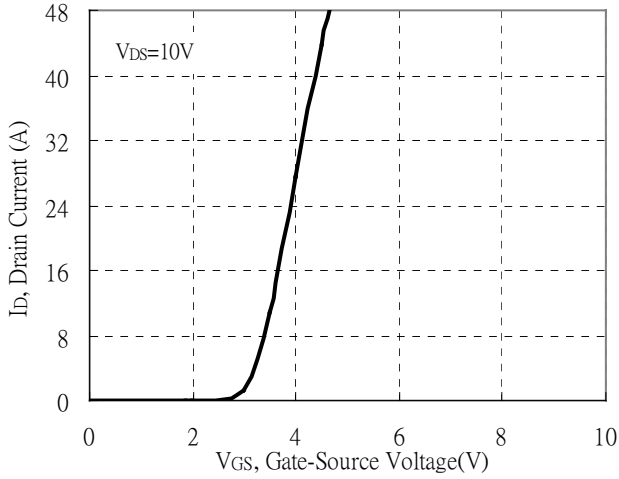
Maximum Drain Current vs Junction Temperature



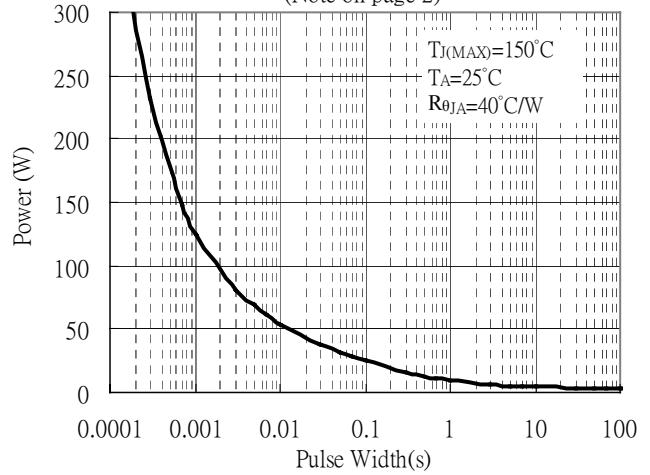


Typical Characteristics(Cont.)

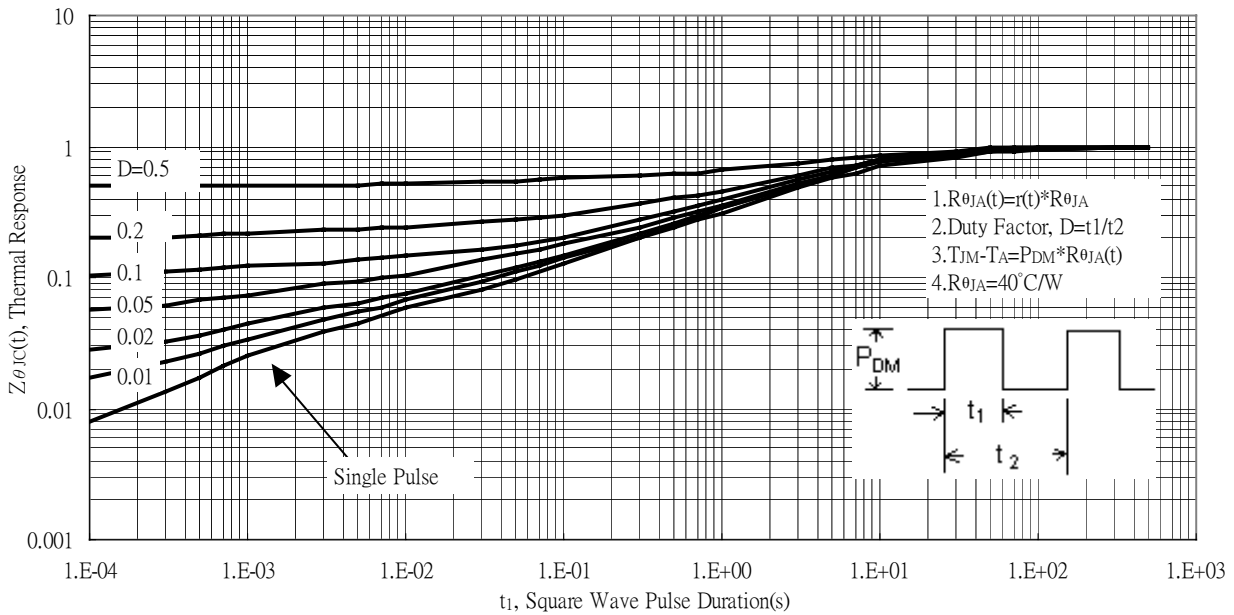
Typical Transfer Characteristics



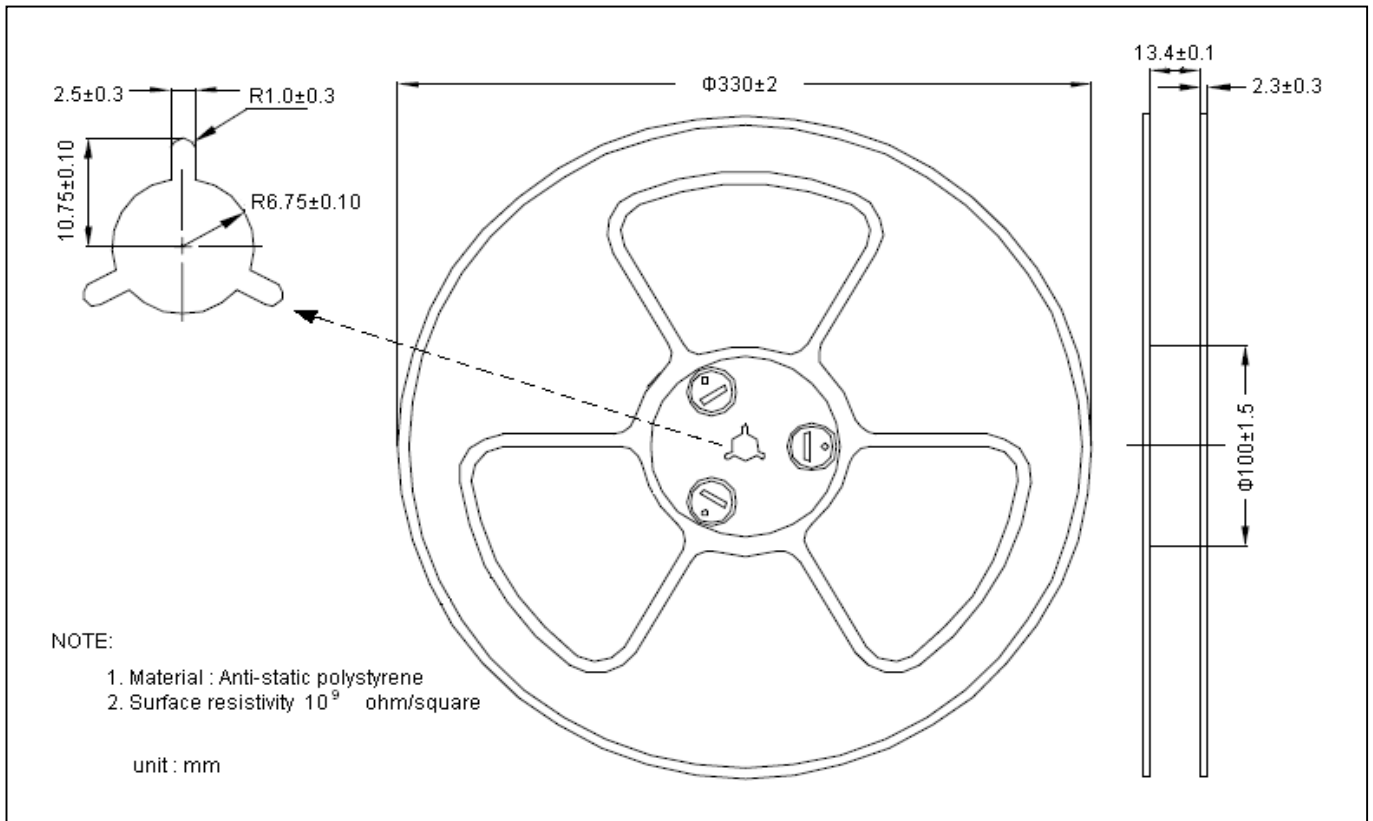
Single Pulse Power Rating, Junction to Ambient
(Note on page 2)



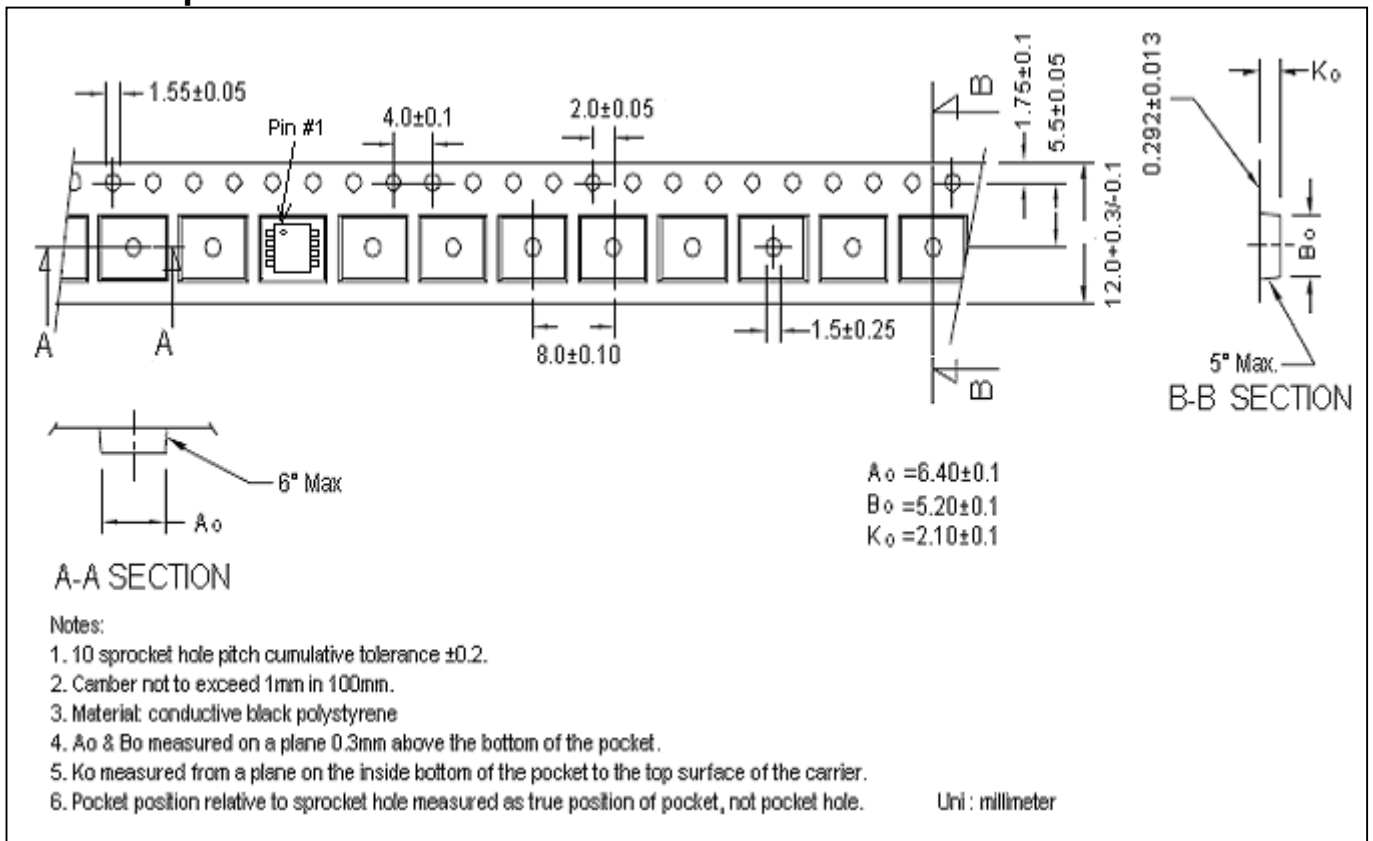
Transient Thermal Response Curves



Reel Dimension



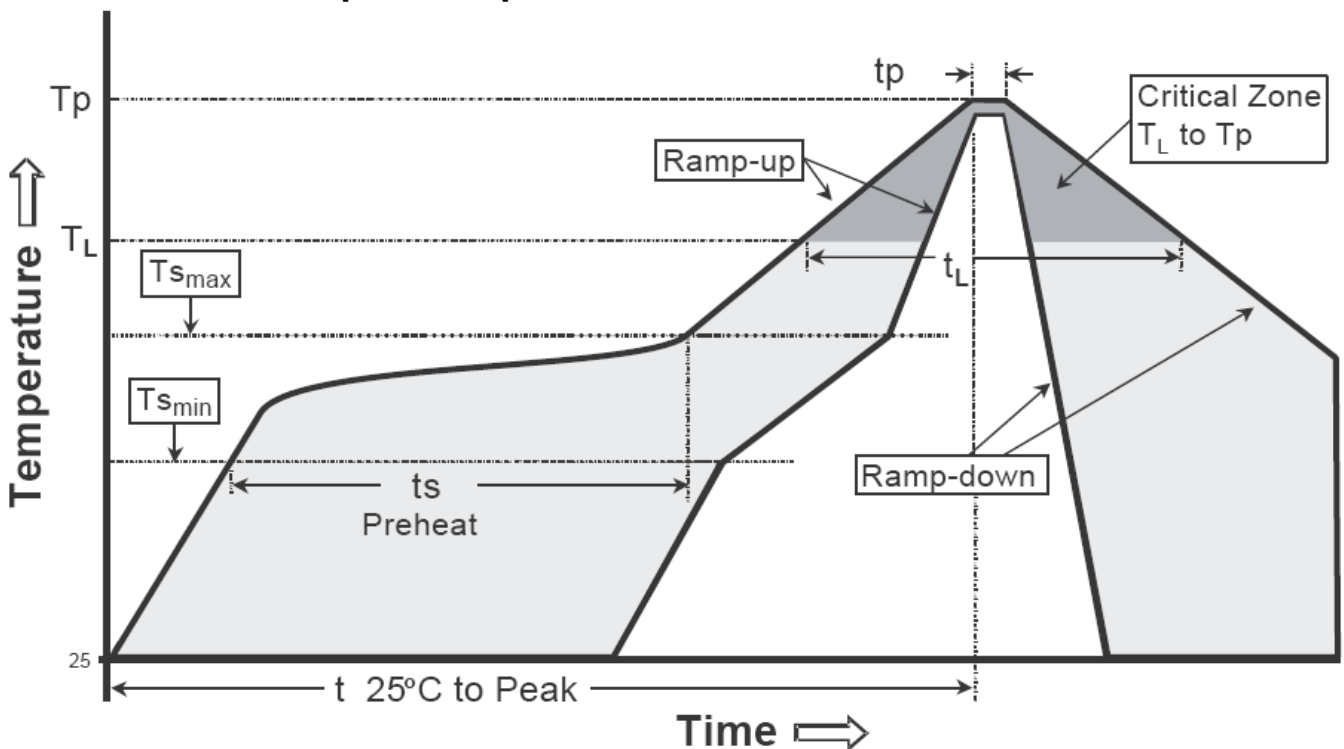
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

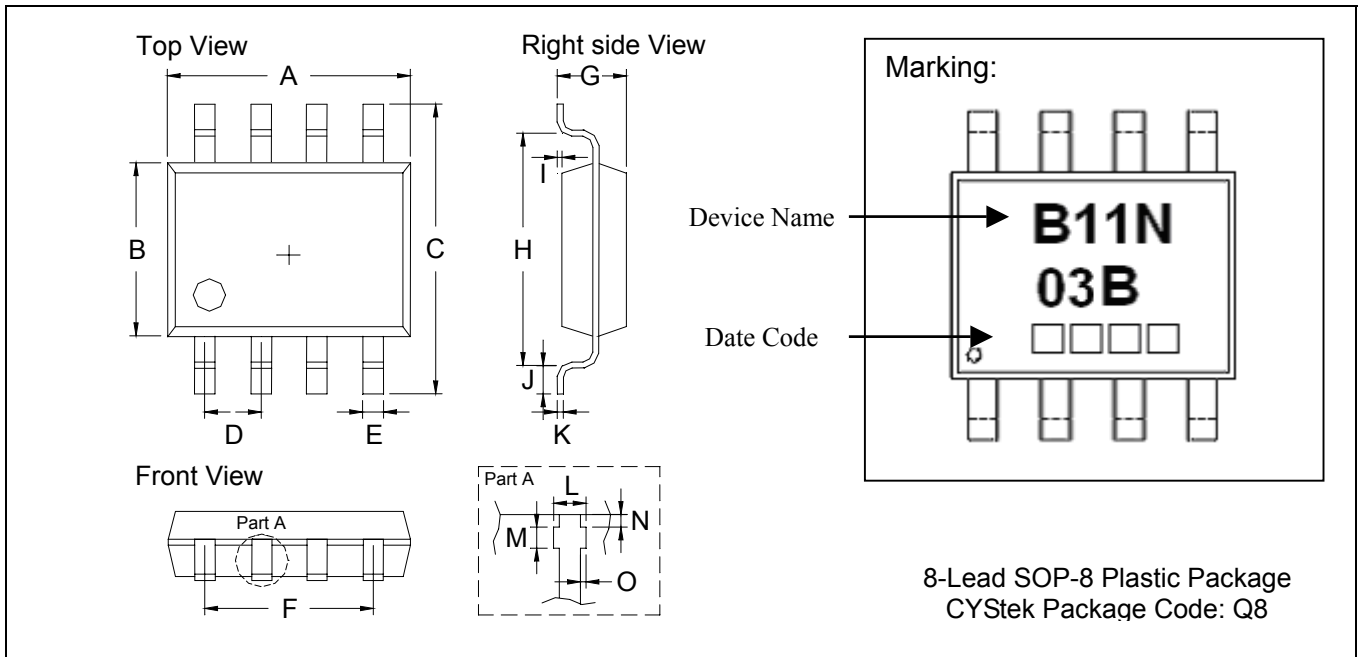
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (Tl)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(Tp)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOP-8 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1909	0.2007	4.85	5.10	I	0.0019	0.0078	0.05	0.20
B	0.1515	0.1555	3.85	3.95	J	0.0118	0.0275	0.30	0.70
C	0.2283	0.2441	5.80	6.20	K	0.0074	0.0098	0.19	0.25
D	0.0480	0.0519	1.22	1.32	L	0.0145	0.0204	0.37	0.52
E	0.0145	0.0185	0.37	0.47	M	0.0118	0.0197	0.30	0.50
F	0.1472	0.1527	3.74	3.88	N	0.0031	0.0051	0.08	0.13
G	0.0570	0.0649	1.45	1.65	O	0.0000	0.0059	0.00	0.15
H	0.1889	0.2007	4.80	5.10					

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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